

which boron atoms were subsequently placed. The *R*-factor then dropped to 20.4%. These additional positions indicate an excess of sites, which can be attributed to a statistical distribution of inter-icosahedral atoms; also, aluminum has not yet been positioned. The exact distribution of the inter-icosahedral atoms is a matter for three-dimensional analysis, which is in progress.

The icosahedra are centered at 4(c) with the coordinates $x/a, y/b, z/c = 0.1, 0.25, 0; 0.9, 0.75, 0; 0.6, 0.25, 0.50$, and $0.4, 0.75, 0.50$.

The symmetry required of the B_{12} configuration by the space group is $mm2$, and no conclusion can be drawn at this time as to what degree the symmetry mmm of a regular icosahedron is approximated. Within the icosahedra, preliminary bond distance calculations reveal boron-boron distances ranging from 1.77 to 1.91 Å., in agreement with bond lengths reported for elementary boron.

U. S. ARMY ELECTRONICS RESEARCH AND DEVELOPMENT LABORATORY
FORT MONMOUTH, NEW JERSEY

GEORG WILL

RECEIVED MAY 10, 1963

High Resolution Nuclear Magnetic Resonance Spectra of Methylsilicon Compounds

Sir:

There is considerable current interest in the correlation between spin-spin coupling constants and hybridization of the atoms participating in the chemical bondings of the compounds studied. A series of important relations have been established for a number of organic¹⁻⁸ and tin-organic^{9,10} compounds, using the indirect spin-spin interaction of ¹³C and ^{117,119}Sn with protons as a reference. In recent papers^{6,11} these investigations were extended to the interactions of the ²⁹Si isotope (natural abundance 4.7%, spin 1/2) with protons directly bonded to silicon, but the results are not yet as readily understood in terms of hybridization.

¹H-²⁹Si interactions in compounds with protons not directly bonded to silicon, however, are not easily detected in n.m.r. spectra of ordinary resolution because of the small coupling constants, and corresponding data are known only for a small number of organosilicon compounds.^{7,11,12} As a part of our current high resolution n.m.r. studies on alkylsilicon compounds this communication now reports the H-C-²⁹Si and H-¹³C coupling constants of some series of methylsilicon derivatives, which show significant dependence on the nature of the ligands attached to the central silicon atom.

The chemical shifts and coupling constants of tetramethylsilane (I) and the four trimethylsilicon halides (II-V), given in Table I, show a marked decrease in the δ values and an increase in $J(\text{H}-^{13}\text{C})$ and $J(\text{H}-\text{C}-^{29}\text{Si})$ in the sequence $\text{CH}_3, \text{F}, \text{Cl}, \text{Br}, \text{I}$. These relations are in contradiction to customary electronegativity considerations ($\text{F} > \text{Cl} > \text{Br} > \text{I} > \text{CH}_3$), from which an opposite trend should be expected. (Proton shielding usually is restricted by an increasing electronegativity of the substituent introduced in a compound, and the spin-spin interactions should be greater

- (1) M. F. Ramsey, *Phys. Rev.*, **91**, 303 (1953).
- (2) M. Karplus and D. H. Anderson, *J. Chem. Phys.*, **30**, 6 (1959).
- (3) J. N. Shoolery, *ibid.*, **30**, 1427 (1959).
- (4) N. Muller and D. E. Pritchard, *ibid.*, **30**, 768, 1471 (1959).
- (5) E. R. Malinowsky, *J. Am. Chem. Soc.*, **83**, 4479 (1961).
- (6) C. Juan and H. S. Gutowsky, *J. Chem. Phys.*, **37**, 2198 (1962).
- (7) H. S. Gutowsky and C. Juan, *J. Am. Chem. Soc.*, **84**, 307 (1962).
- (8) G. Klose, *Ann. Physik*, **9**, 262 (1962).
- (9) J. R. Holmes and H. D. Kaesz, *J. Am. Chem. Soc.*, **83**, 3903 (1961).
- (10) G. P. van der Kelen, *Nature*, **193**, 1069 (1962).
- (11) E. A. V. Ebsworth and J. J. Turner, *J. Chem. Phys.*, **36**, 2628 (1962).
- (12) G. Fritz, E. A. V. Ebsworth, *et al.*, *Z. anorg. allgem. Chem.*, **321**, 10 (1963).

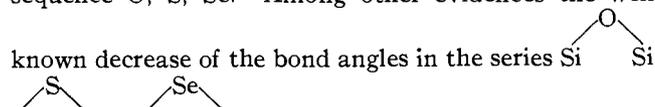
TABLE I
CHEMICAL SHIFTS δ AND COUPLING CONSTANTS J OF SOME TRIMETHYLSILICON DERIVATIVES

Varian A-60, 60 Mc., room temperature, TMS as an internal reference. All compounds in CCl_4 with $c = 5 \pm 1\%$ [v./v.] for δ , and $c = 20 \pm 2\%$ [v./v.] for J values. Standard deviations are ± 1 [c.p.s.] for δ , $J(\text{H}-^{13}\text{C})$, and $J(\text{H}-\text{C}-\text{Sn}, \text{Pb})$, and ± 0.05 [c.p.s.] for $J(\text{H}-\text{C}-^{29}\text{Si})$ and $J(\text{H}-\text{C}-\text{Si}-\text{F})$.

No.	Formula	δ^a	J (H- ¹³ C)	$J(\text{H}-\text{C}-^{29}\text{Si})$
I	Me ₄ Si	0.0	118.5	6.78
II	Me ₃ SiF ^a	-12.2	118.8	7.00
III	Me ₃ SiCl	-25.4	120.5	7.10
IV	Me ₃ SiBr	-42.5	121.0	7.23
V	Me ₃ SiI	-47.0	121.5	7.30
VI	Me ₃ SiOSiMe ₃	-3.5	118.0	6.86
VII	Me ₃ SiSSiMe ₃	-19.5	119.5	7.10
VIII	Me ₃ SiSeSiMe ₃	-25.7	120.5	7.15
IX	Me ₃ SiOGeMe ₃	Me ₃ Si	0.0	117.8
		Me ₃ Ge	-21.0	126.0
X	Me ₃ SiOSnMe ₃ ^b	Me ₃ Si	+2.5	116.8
		Me ₃ Sn	-20.5	128.5
XI	Me ₃ SiOPbMe ₃ ^c	Me ₃ Si	+3.5	115.5
		Me ₃ Pb	-73.0	136.0
XII	(Me ₃ Si) ₃ N	-10.7	118.0	6.76
XIII	(Me ₃ Si) ₂ NGeMe ₃	Me ₃ Si	-7.2	118.0
		Me ₃ Ge	-23.5	125.4
XIV	(Me ₃ Si) ₂ NSnMe ₃ ^d	Me ₃ Si	-5.0	118.0
		Me ₃ Sn	-18.8	130.0
XV		Me ₃ Si	0.0	117.5
		Me ₃ Si	-14.0	118.5
XVI		Me ₃ Si	0.0	118.5
		Me ₃ Si	-15.0	119.0
XVII	[(Me ₃ SiO) ₂ Al] ₂	bridges	-19.0	119.0
		terminal	-4.0	116.0

^a $J(\text{HCSiF}) = 7.48$. ^b $J(\text{H}-\text{C}-^{117,119}\text{Sn}) = 54.9, 57.4$.
^c $J(\text{H}-\text{C}-^{207}\text{Pb}) = 69.5$. ^d $J(\text{H}-\text{C}-^{117,119}\text{Sn}) = 53.4, 55.8$. ^e In c.p.s., negative values are downfield of TMS.

in the compound having the most polarized silicon-halogen bonding, which would lead the central silicon atom to a maximum $sp^3 \rightarrow sp^2$ rehybridization.) From these considerations trimethylfluorosilane should show the lowest chemical shielding and the highest J -values. The results are readily explained, however, by the assumption of a systematic decrease of $d\pi-p\pi$ -interactions between silicon and the halogens, the magnitude of which is a function of the relative atomic radii of the atoms. These π -interactions provide an increase in polarity of the Si-halogen bonding in the direction $\text{F} < \text{Cl} < \text{Br} < \text{I}$ ("back-donation") and an increase in s -character of the silicon and even the carbon orbitals, being in close relation with each other by the Si-C-bondings, following this sequence. Similar results were obtained for hexamethyldisiloxane and its analogs (VI-VIII),¹³ as presented in the table, and can be interpreted in a corresponding manner, following the sequence O, S, Se. Among other evidences the well

known decrease of the bond angles in the series Si  Si is a good support for this assumption.¹⁴

Tris-trimethylsilylamine (XII) and the cyclic trisilylamine compounds XV and XVI¹⁵ gave surprisingly low values for the Me₃Si- groups and illustrate the unusual

(13) For Me₃SiSeSiMe₃ see: M. Schmidt and H. Ruf, *Z. anorg. allgem. Chem.*, **32**, 270 (1963).

(14) R. J. Gillespie, *J. Am. Chem. Soc.*, **82**, 5978 (1960).

(15) W. Fink, *Angew. Chem.*, **73**, 736 (1961), and *Helv. Chim. Acta*, **46**, 720 (1963); We thank Dr. Fink for providing the samples.

